

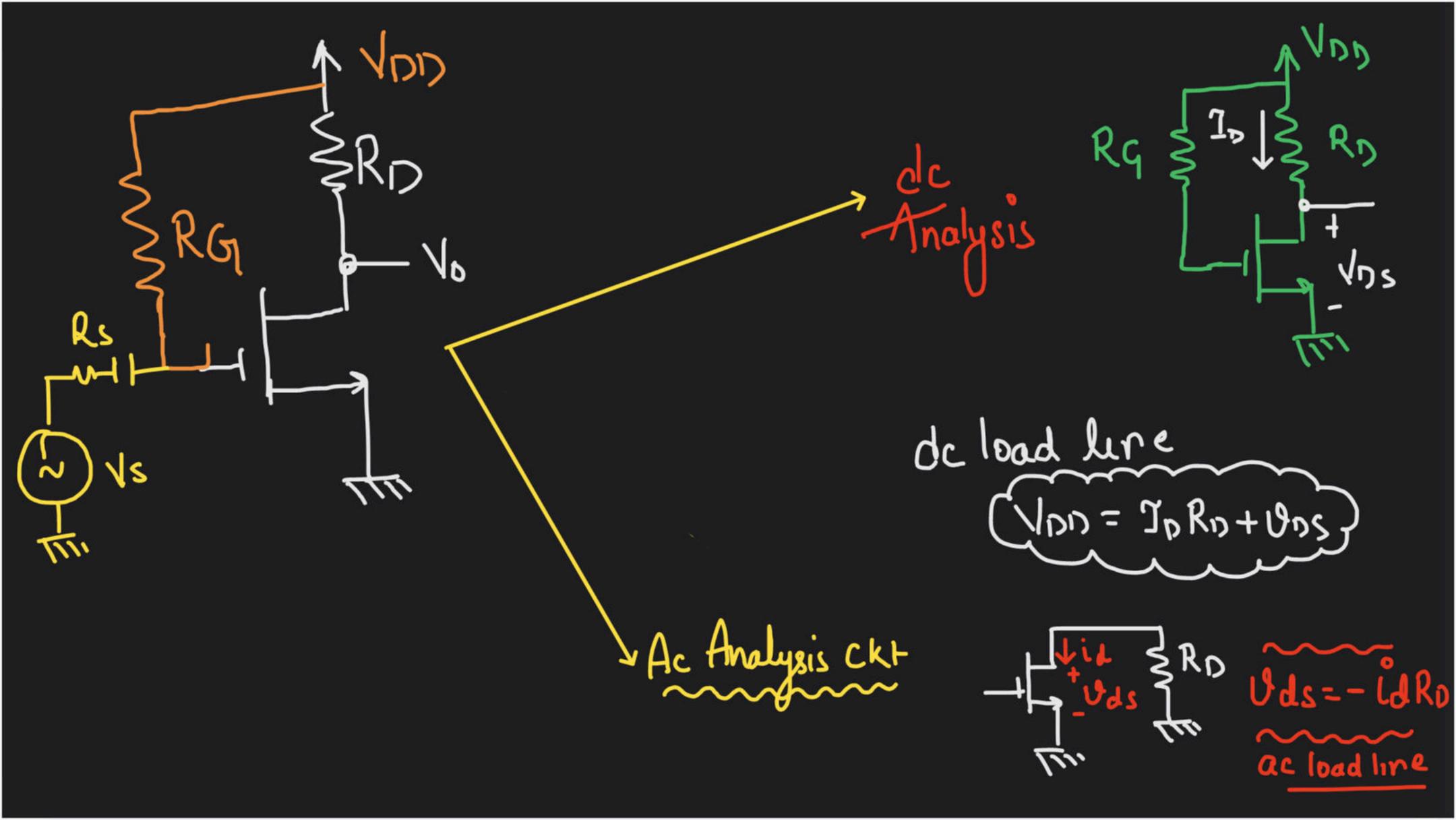
Lakshya GATE 2023: Course on Analog Electronics for ECE EE IN

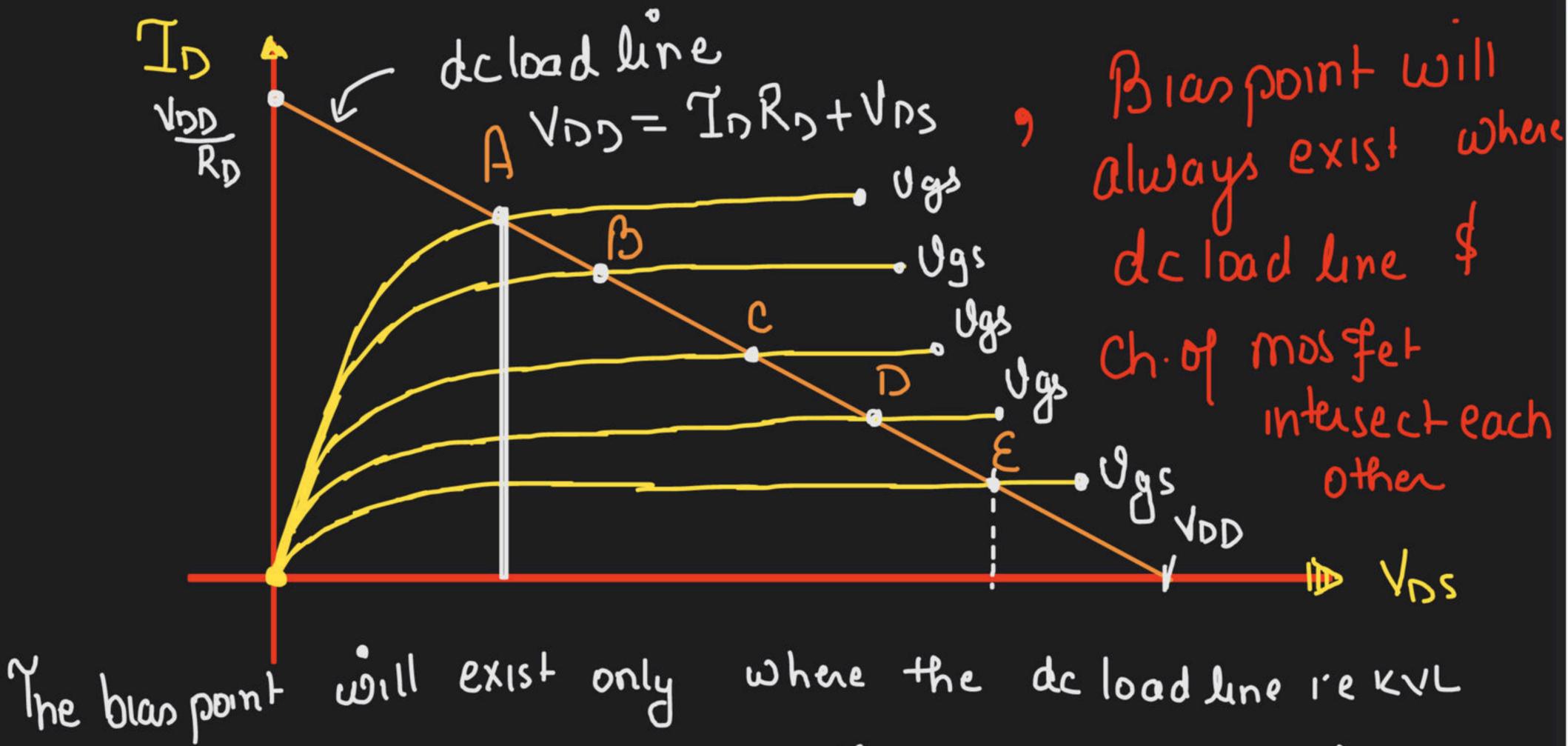
Falends

Topic: - Ac and Dc load line

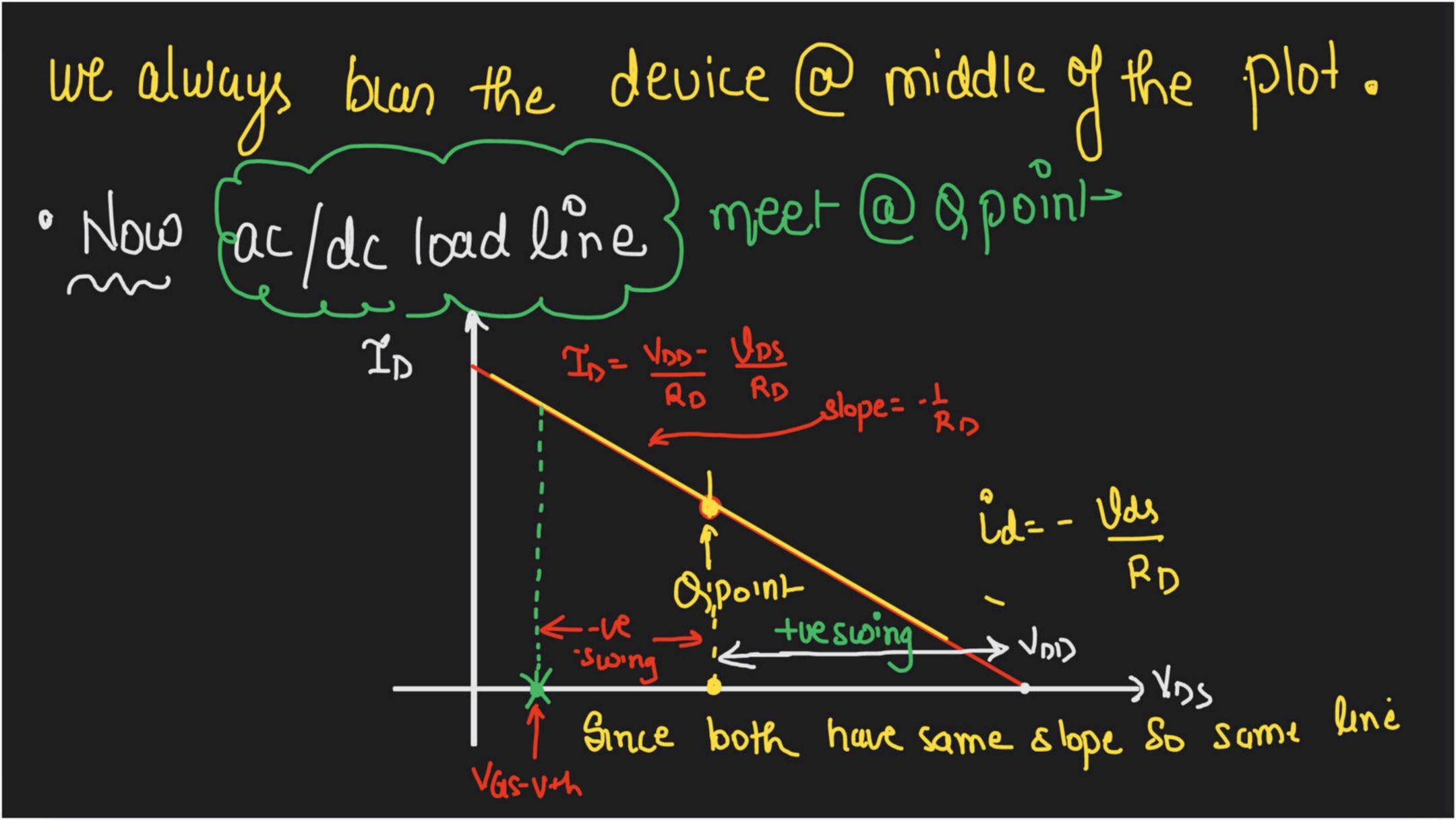
=> The Blan point of Mosfet [ID, Vos],

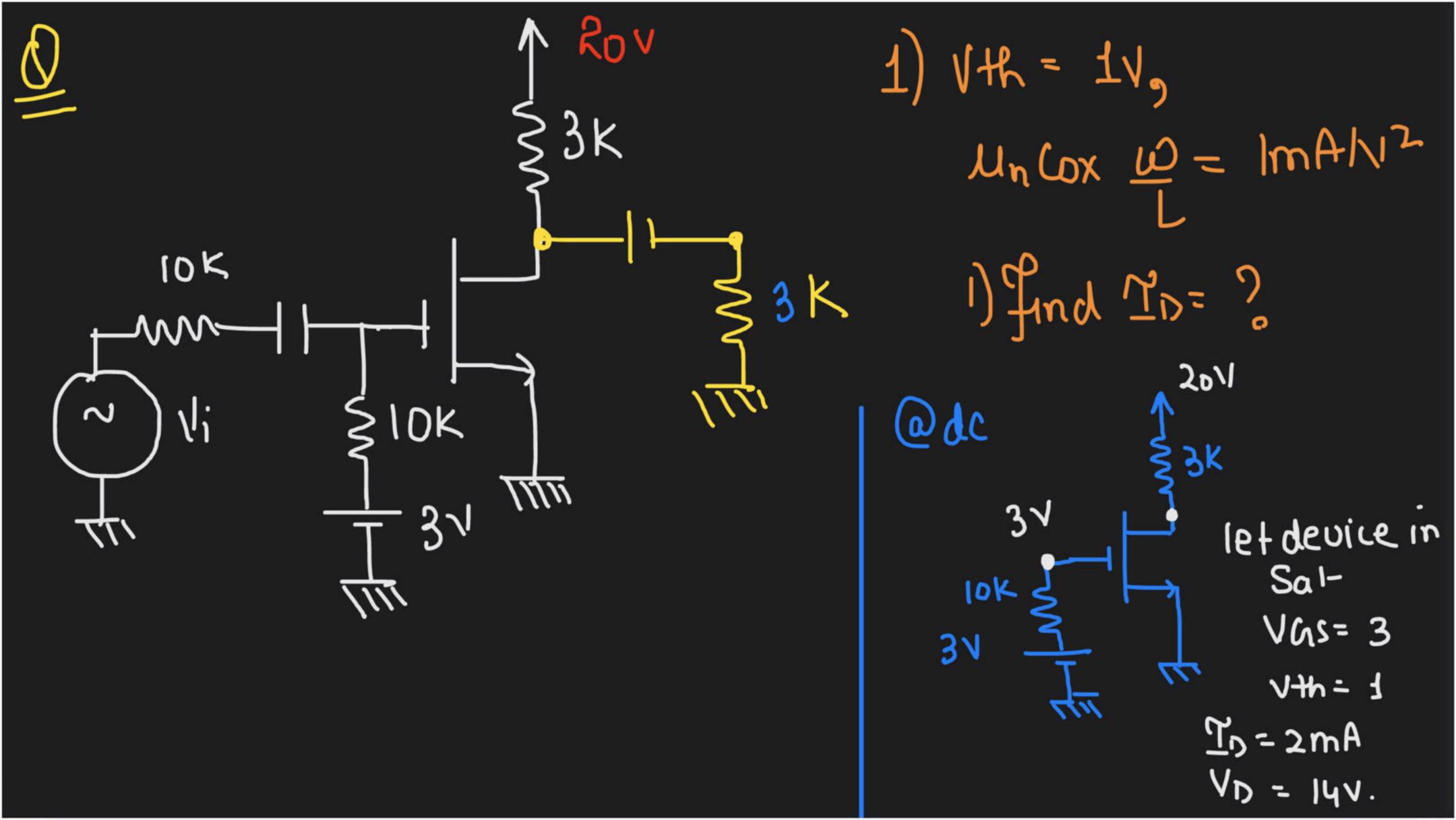
Example



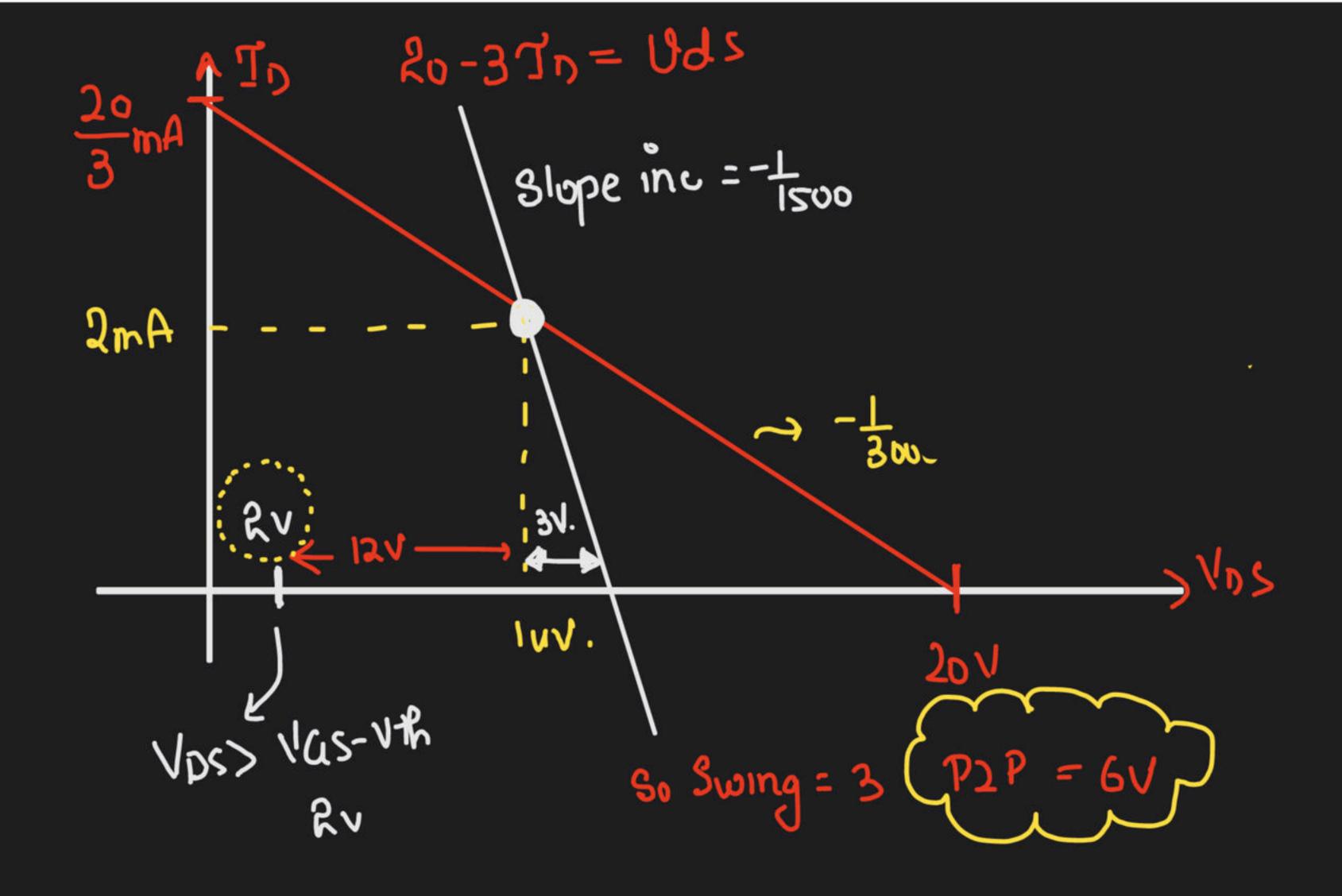


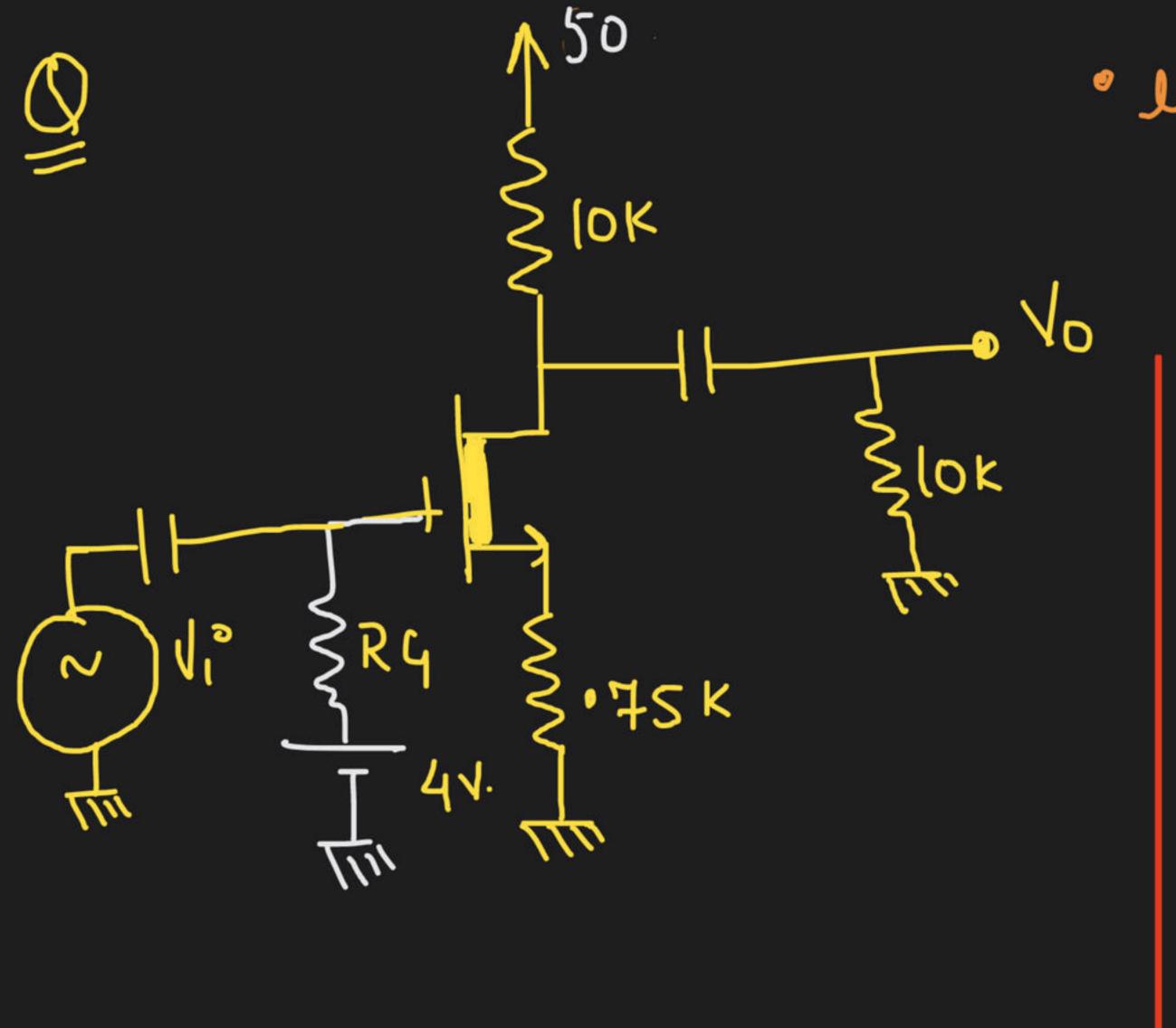
and mosfer ch. are satisfied i.e they both cut each other





Biaspoint => 
$$I_D$$
,  $V_D$ s  $(2mA_9 14V)$ 





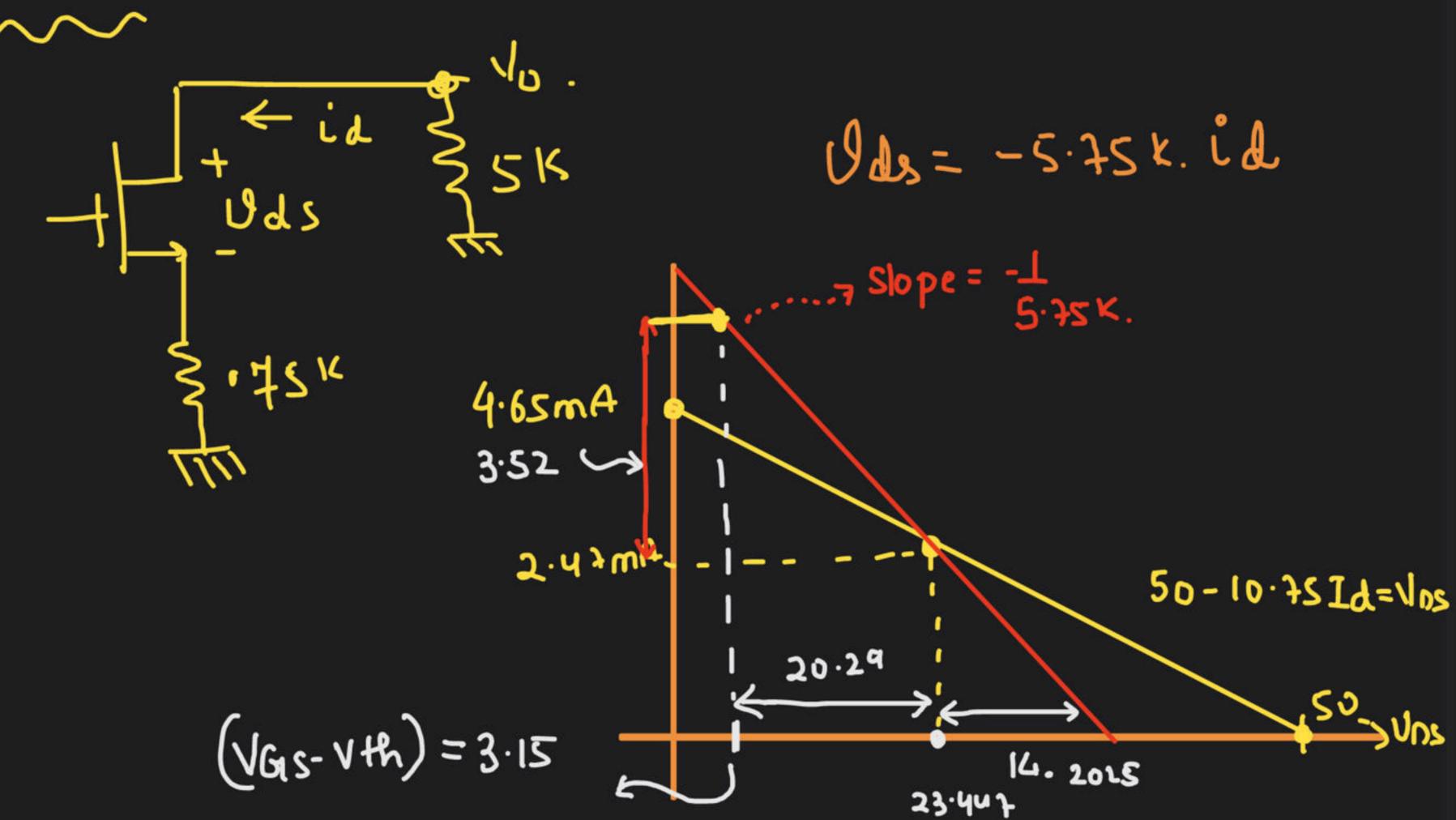
· Unlox w = ·5mA/V

· Uth = - 1V

$$T_0 = \frac{1}{2} \times .5 \left( 4 - .35 I_0 - (-1) \right)^{-1}$$

$$\sqrt{105} = 50 - (10.75 \times 2.47)$$
 $\sqrt{105} = 23.447$ 
 $\sqrt{105} = 23.447$ 
 $\sqrt{105} = 4.4595 = 2.14$ 

Now CKH@ oc



Ld Swing 2.47 mA 1905-5000 id duing @ 1/0 = +12:35 P2P= 24.74

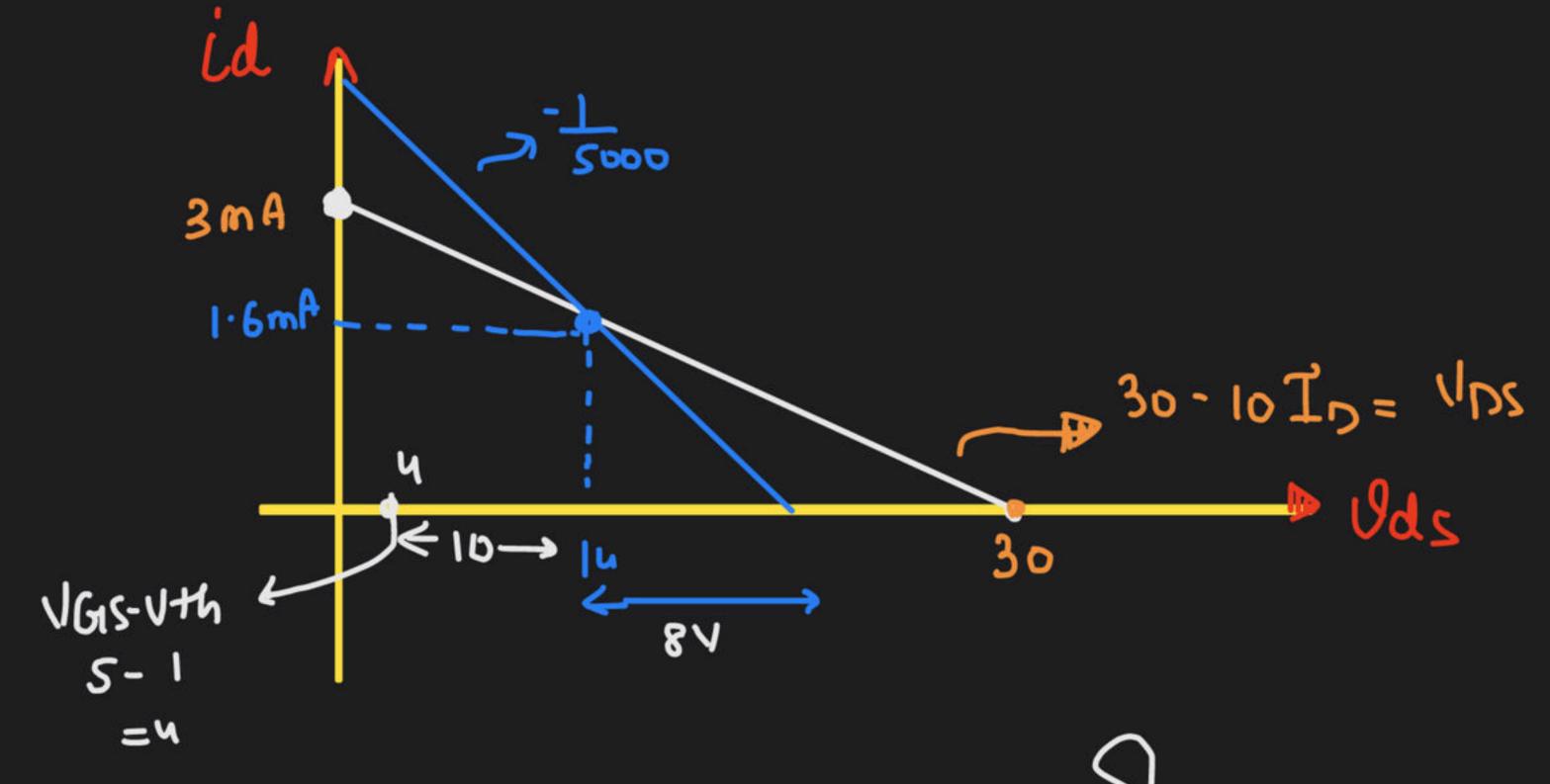
130V Vth= 1V, un cox w = .2m4/12IOK · 1) Swing available @ % c) 12 d)10 16 (de

$$T_{0} = \frac{1}{2} u_{n} (o_{x} \frac{\omega}{U} (5-1)^{2}$$

$$= \frac{1}{2} \times 2 (u)^{2} = 1.6 mA$$

$$\sqrt{0} = 14V.$$

ac Analysis



Offind allowed Swing of input Signal =).

a) 8
b) 6
4
d) 2

$$g_{m} = \int_{Z} u_{n} \omega_{x} \frac{\pi}{2} x \frac{\pi}{2}$$

$$= \int_{Z} x_{1:6} y_{10}^{-3} x \cdot 2x_{10}^{-3} x$$

$$g_{m} = 8x_{10}^{-4} y$$

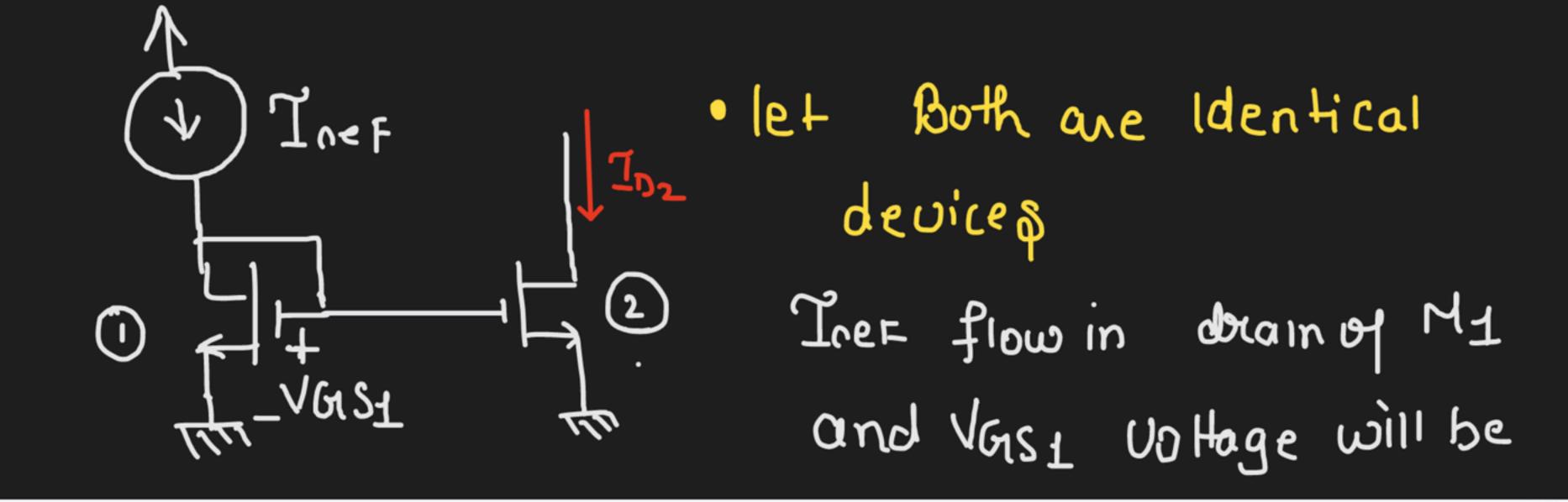
$$V_{0} = -g_{m} U_{g} \leq 5000$$

$$= -8x_{10}^{-4} x + 2x_{2} \leq 5000 U_{1}^{-3}$$

$$V_{0} = -2U_{1}^{-3}$$

## Topic Couvrent Misurur Using Moefet

The Basic Curvent mi rook =>



Here 
$$VGISI = VGISZ$$
 thus

assume that

M\_ISIN

Sa+ Mode

device are Same

80 There = Toz



Lakshya GATE 2023: Course on Analog Electronics for ECE EE IN

# De Find Curent ID

- Uncox w of both device = 1 m Alv2

  Uth = 1
  - · Stepi Both in Sat identical device, Ugs Same

$$5 = 2098$$

$$\frac{095 = 2.5}{100}$$

$$\frac{1}{2} \times 1 \times (2.5 - 1)^{2} = 1.125m^{4}$$

Find Is Unlove = 1mAlv TOV. Wh= 1v

Find ID Unlor 1 = 2mt/v I Unlox W= 4mAN 4th= 1V for 60th
ind In.

Since device 8hd be in Sal-

VGD (Vth Va-VD < Vth 10 > VG-VHh Vps> Vas- Uth

## unacademy

### Asked by Anisha

Please help me with this doubt

### Common Data For Q. 5 and 6:

A p-channel depletion mode MOSFET has the following parameters

$$K_p = 0.5 \text{ mA/V}^2, V_{TH} = 2 \text{ V}$$

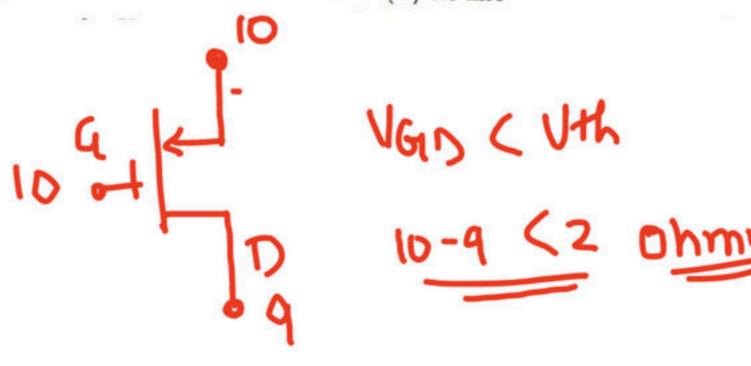
If  $V_{SG} = 0$ , current  $I_D$  for  $V_{SD} = 1$  V is MCQ 4.1.5

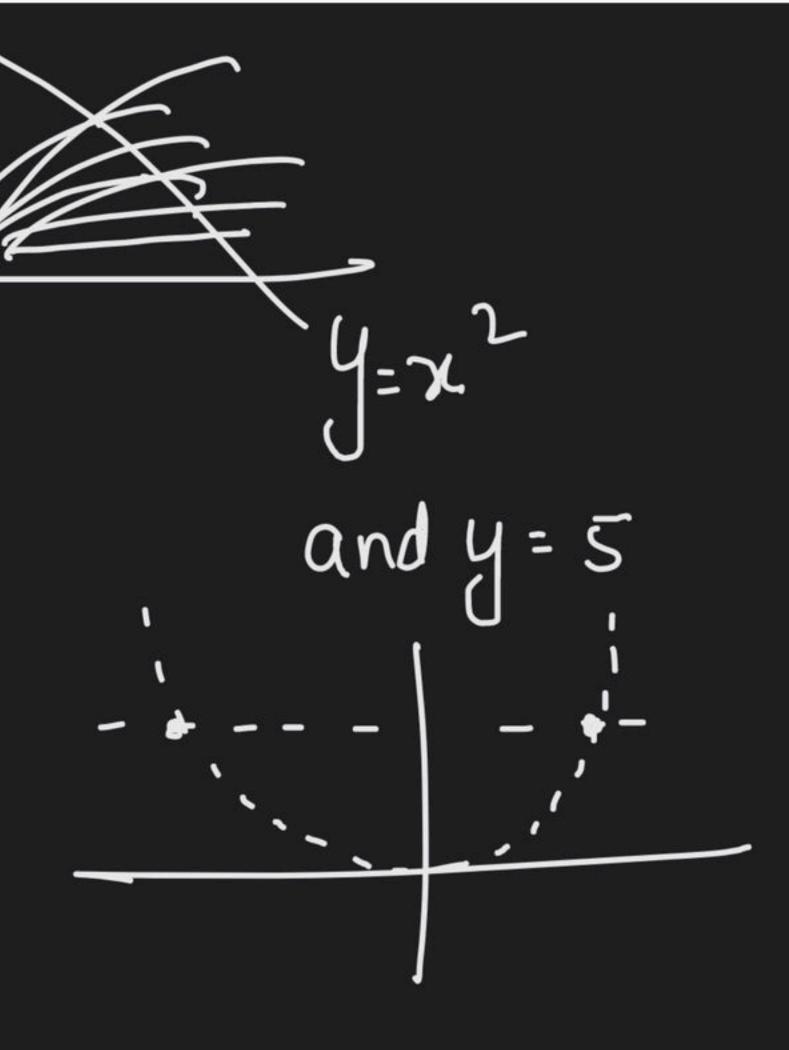
(A) 0 mA

(B) 1.5 mA

(C) 2 mA

(D) 0.5 mA









### unacademy

### ▲ 1 • Asked by Yuvraj

ouput resistance mai problem hai???

